

Triac Medium Power Use

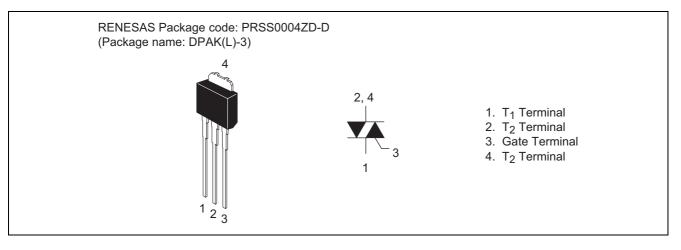
> REJ03G0291-0200 Rev.2.00 Nov 30, 2007

Features

- $I_{T(RMS)}: 5 A$
- V_{DRM} : 600 V
- www.DataSheet $U.I_{FGTI}^{ORM}$, I_{RGTI} , I_{RGTI} , I_{RGT} III : 30 mA

- Non-Insulated Type
- Planar Passivation Type
- Lead Mounted Type

Outline



Applications

Hybrid IC, solid state relay, switching mode power supply, light dimmer, electric fan, electric blanket, washing machine, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Faialletei	Symbol	12		
Repetitive peak off-state voltage ^{Note1}	V _{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V _{DSM}	720	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	5	A	Commercial frequency, sine full wave 360° conduction, Tc = $103^{\circ}C^{Note3}$
Surge on-state current	I _{TSM}	50	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	10.4	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	3	W	
Average gate power dissipation	P _{G (AV)}	0.3	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	2	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
eMassim		0.26	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	_	—	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V _{TM}	_	—	1.8	V	$Tc = 25^{\circ}C$, $I_{TM} = 7 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	Ι	V _{FGTI}	_		1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V _{RGTI}	_	—	1.5	V	R _G = 330 Ω
	III	V _{RGTIII}	_	—	1.5	V	
Gate trigger current ^{Note2}	Ι	I _{FGTI}	_	—	30	mA	$\label{eq:tilde} \begin{split} Tj &= 25^\circ C, \ V_D = 6 \ V, \ R_L = 6 \ \Omega, \\ R_G &= 330 \ \Omega \end{split}$
	II	I _{RGTI}	_	—	30	mA	
	III	I _{RGTIII}	_	—	30	mA	
Gate non-trigger voltage		V _{GD}	0.2	—	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	—	3.0	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-staticommutating voltage ^{Note4}	e	(dv/dt)c	5	—	_	V/µs	Tj = 125°C

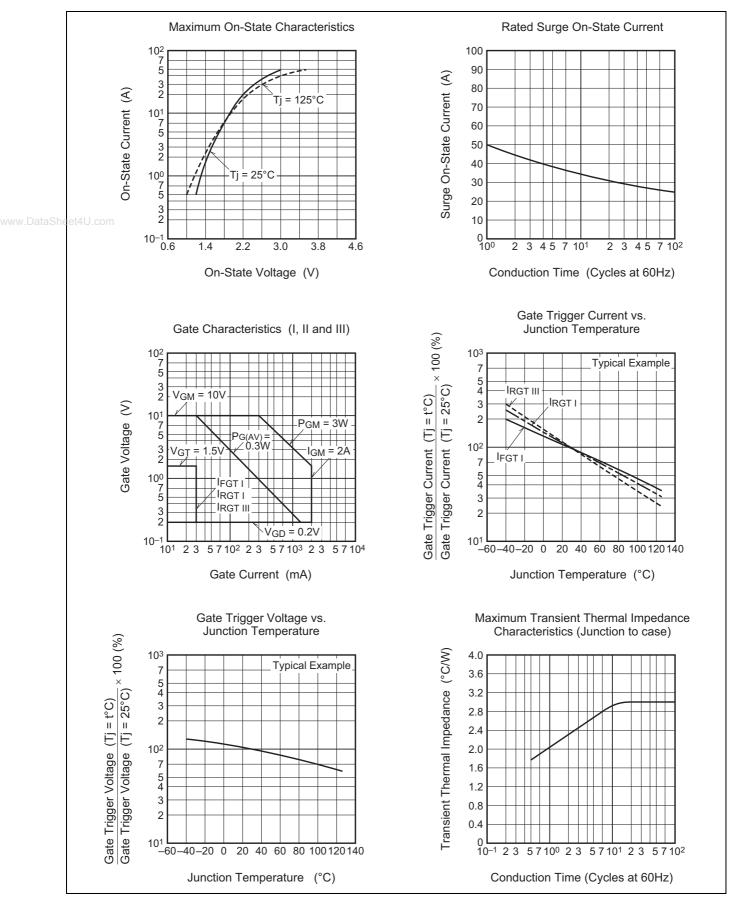
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured on the T_2 tab.

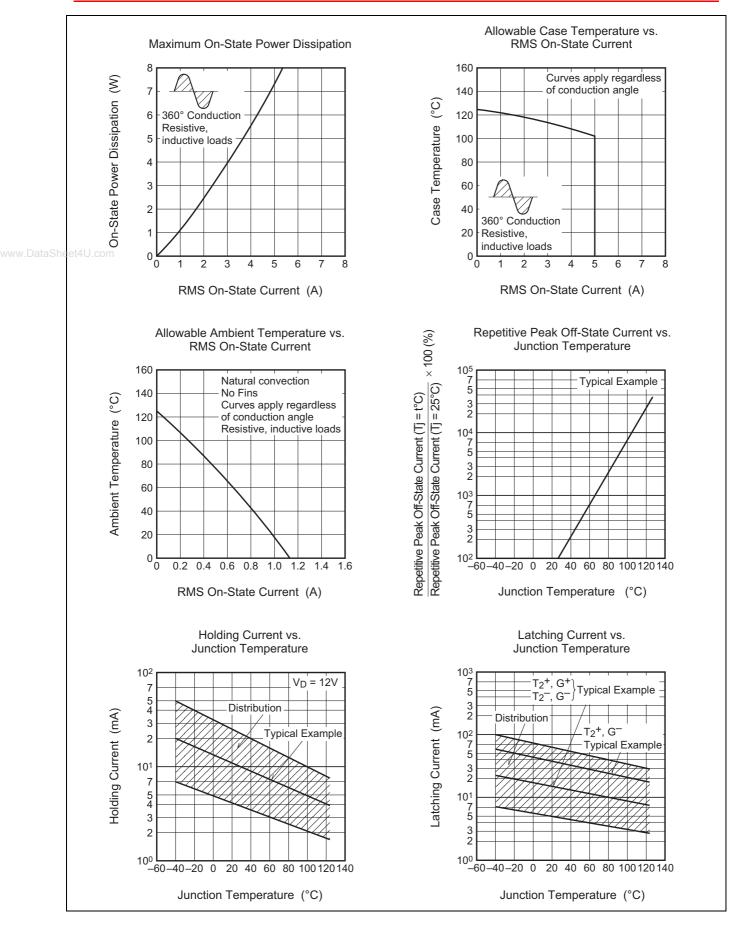
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage → Time		
 Rate of decay of on-state commutating current (di/dt)c = -2.5 A/ms 	Main Current → Time		
3. Peak off-state voltage V _D = 400 V	Main VoltageTime (dv/dt)c V _D		

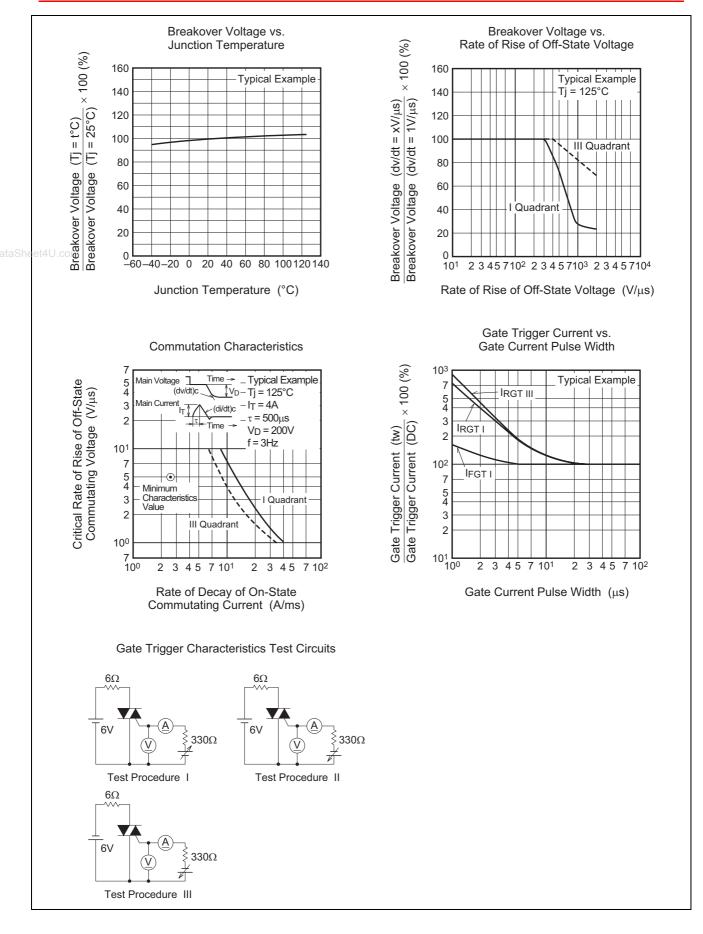
Performance Curves



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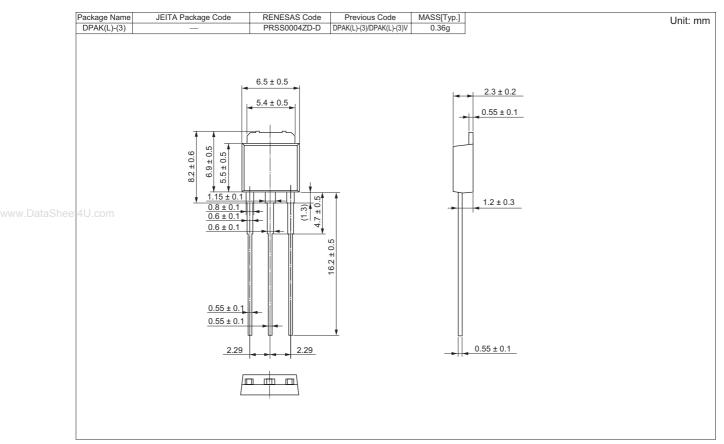


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Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name – A1	BCR5AS-12A-A1

Note : Please confirm the specification about the shipping in detail.

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